Download Molecular Beam Epitaxy A Short History

This book describes the development of MBE from its origins in the 1960s through to the present day. It begins with a short historical account of other methods of crystal growth, both bulk and epitaxial, to set the subject in context, emphasising the wide range of semiconductor materials employed.

The book is a history of Molecular Beam Epitaxy (MBE) as applied to the growth of semiconductor thin films (note that it does not cover the subject of metal thin films).

What is molecular beam epitaxy? Photo: Molecular beam epitaxy (MBE) in action. MBE takes place in ultra-high vacuum (UHV) chambers like this, at temperatures of around 500°C (932°F), to ensure a totally clean, dust-free environment; the slightest contamination could ruin the crystal. Photo by Jim Yost courtesy of US DOE/NREL (U.S. Department of Energy/National Renewable Energy Laboratory).

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Molecular Beam Epitaxy A Short History John Orton and Tom Foxon. Unique text on the history of Molecular Beam Epitaxy; Increases understanding of how semiconductor science and technology have developed

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Molecular-beam epitaxy (MBE) is an epitaxy method for thin-film deposition of single crystals. The MBE process was developed in the late 1960s at Bell Telephone Laboratories by J. R. Arthur and Alfred Y. Cho .

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